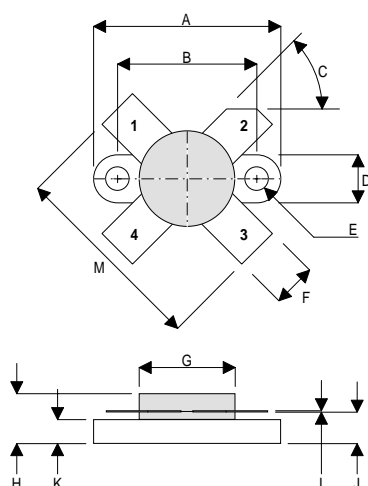


## MECHANICAL DATA



## DMX

PIN 1	SOURCE	PIN 2	DRAIN
PIN 3	SOURCE	PIN 4	GATE

DIM	mm	Tol.	Inches	Tol.
A	28.83	0.13	1.135	0.005
B	21.97	0.13	0.865	0.005
C	45°	5°	45°	5°
D	6.86	0.13	0.27	0.005
E	3.43 Dia.	0.13	0.135 Dia.	0.005
F	5.84	0.13	0.230	0.005
G	13.97 Dia.	0.13	0.550 Dia.	0.005
H	6.60	REF	0.260	REF
I	0.13	0.02	0.005	0.001
J	3.81	0.25	0.15	0.01
K	2.54	0.13	0.100	0.005
M	27.94	0.51	1.10	0.02

## GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 300W – 50V – 30MHz SINGLE ENDED

## FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 20 dB MINIMUM

## APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS  
from 1 MHz to 175 MHz

### ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$ unless otherwise stated)

$P_D$	Power Dissipation	500W
$BV_{DSS}$	Drain – Source Breakdown Voltage	125V
$BV_{GSS}$	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	36A
$T_{stg}$	Storage Temperature	$-65$ to $150^{\circ}C$
$T_j$	Maximum Operating Junction Temperature	$200^{\circ}C$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS Drain–Source Breakdown Voltage	V <sub>GS</sub> = 0      I <sub>D</sub> = 100mA	125			V
I <sub>D</sub> DSS Zero Gate Voltage Drain Current	V <sub>DS</sub> = 50V      V <sub>GS</sub> = 0			12	mA
I <sub>G</sub> DSS Gate Leakage Current	V <sub>GS</sub> = 20V      V <sub>DS</sub> = 0			12	μA
V <sub>GS(th)</sub> Gate Threshold Voltage*	I <sub>D</sub> = 10mA      V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub> Forward Transconductance*	V <sub>DS</sub> = 10V      I <sub>D</sub> = 6A	9.6			S
G <sub>PS</sub> Common Source Power Gain	P <sub>O</sub> = 300W	20			dB
η Drain Efficiency	V <sub>DS</sub> = 50V      I <sub>DQ</sub> = 1.2A	50			%
VSWR Load Mismatch Tolerance	f = 30MHz	20:1			—
C <sub>iss</sub> Input Capacitance	V <sub>DS</sub> = 50V      V <sub>GS</sub> = -5V      f = 1MHz			720	pF
C <sub>oss</sub> Output Capacitance	V <sub>DS</sub> = 50V      V <sub>GS</sub> = 0      f = 1MHz			300	pF
C <sub>rss</sub> Reverse Transfer Capacitance	V <sub>DS</sub> = 50V      V <sub>GS</sub> = 0      f = 1MHz			18	pF

\* Pulse Test:    Pulse Duration = 300 μs , Duty Cycle ≤ 2%

### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 0.35°C / W
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